

Title (en)

METHOD AND DEVICE FOR TREATING SEMICONDUCTOR SUBSTRATES

Title (de)

VERFAHREN UND VORRICHTUNG ZUR BEARBEITUNG VON HALBLEITERSUBSTRATEN

Title (fr)

PROCEDE ET DISPOSITIF POUR TRAITER DES SUBSTRATS SEMI-CONDUCTEURS

Publication

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Application

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Abstract (en)

[origin: WO02052617A1] The invention relates to a method and to a device for treating semiconductor substrates. In conventional systems, the especially uncoated semiconductor substrates are fed to a treatment device through a charging sluice (1), said charging sluice (1) adjoining a transfer chamber (2). A plurality of treatment chambers (3, 4, 5) can be charged with the semiconductor substrates to be treated from said transfer chamber by first evacuating the transfer chamber (2) and the treatment chamber (3) and then opening the connecting door (7) between the transfer chamber (2) and the treatment chamber (3). The aim of the invention is to improve this system. To this end, at least one of the treatment chambers (4) is operated at a low pressure or atmospheric pressure and the transfer chamber (2) is flooded with an inert gas before the connecting door (8) associated with the treatment chamber (4) is opened, while a predetermined pressure difference between the transfer chamber and the treatment chamber is maintained.

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